

TO-92L Plastic-Encapsulate Transistors

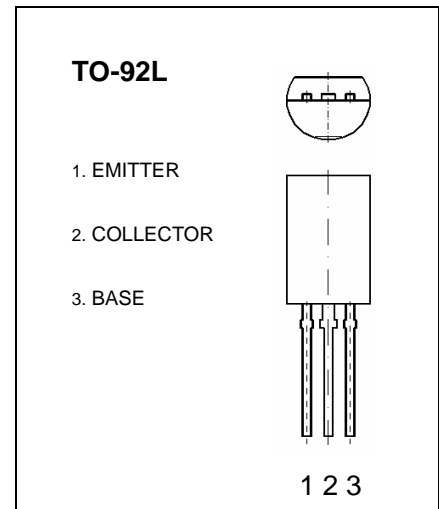
5610 TRANSISTOR (PNP)

FEATURES

- Excellent linearity of Current Gain
- Low saturation voltage
- Complementary to TPT5609

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector- Base Voltage	-25	V
V _{CE0}	Collector-Emitter Voltage	-20	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1	A
P _C	Collector Power Dissipation	0.75	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B = 0	-20			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} = -20V, I _E = 0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -500mA	60		240	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -800mA, I _B = -80mA			-0.5	V
Base-emitter voltage	V _{BE}	V _{CE} = -2V, I _C = -500mA			-1	V
Transition frequency	f _T	V _{CE} = -2V, I _C = -500mA		350		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		38		pF

CLASSIFICATION OF h_{FE}

Rank	A	B	C
Range	60-120	85-170	120-240